# 1. General description

High voltage, high speed, planar passivated NPN power switching transistor with integrated anti-parallel E-C diode in a SOT428 (DPAK) surface mountable plastic package.

## 2. Features and benefits

- Fast switching
- · High voltage capability
- · Integrated anti-parallel E-C diode
- Surface mountable plastic package
- · Very low switching and conduction losses

# 3. Applications

- DC-to-DC converters
- · Electronic lighting ballasts
- Inverters
- Motor control systems

# 4. Pinning information

#### **Table 1. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		C
2	С	collector[1]		
3	E	emitter	DPAK (SOT428)	B — E sym131

[1] It is not possible to make a connection to pin 2 of the SOT428 (DPAK) package.

### NPN power transistor with integrated diode

# 5. Ordering information

#### **Table 2. Ordering information**

Type number	Package				
	Name	Description	Version		
BUJD105AD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428		

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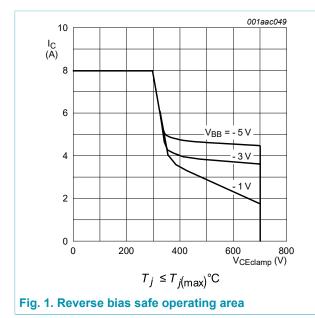
#### NPN power transistor with integrated diode

# 6. Limiting values

#### Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V	-	700	V
$V_{CBO}$	collector-base voltage	I <sub>E</sub> = 0 A	-	700	V
$V_{CEO}$	collector-emitter voltage	I <sub>B</sub> = 0 A	-	400	V
I <sub>C</sub>	collector current	DC; Fig. 1; Fig. 2	-	8	Α
I <sub>CM</sub>	peak collector current	Fig. 1; Fig. 2	-	16	Α
I <sub>B</sub>	base current	DC	-	4	Α
I <sub>BM</sub>	peak base current		-	8	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> ≤ 25 °C; <u>Fig. 3</u>	-	80	W
T <sub>stg</sub>	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C



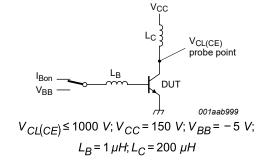


Fig. 2. Test circuit for reverse bias safe operating area

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### NPN power transistor with integrated diode

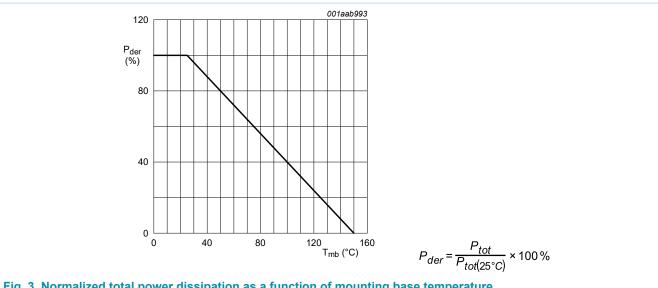


Fig. 3. Normalized total power dissipation as a function of mounting base temperature

#### NPN power transistor with integrated diode

### 7. Thermal characteristics

**Table 4. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	-	1.56	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted; minimum footprint; Fig. 5	-	75	-	K/W

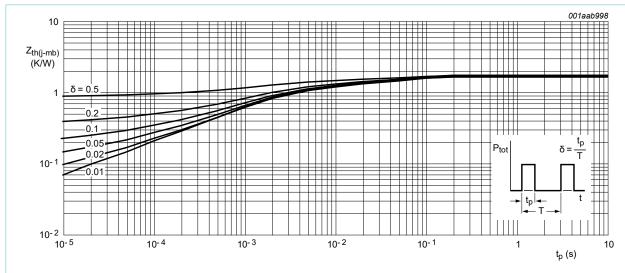


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse width

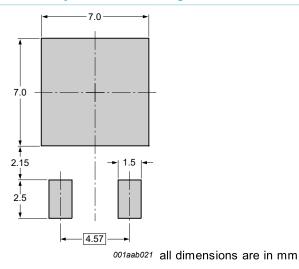


Fig. 5. Minimum footprint SOT428

### NPN power transistor with integrated diode

## 8. Characteristics

Table 5. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	cteristics						
I <sub>CES</sub>	collector-emitter cut-off	V <sub>BE</sub> = 0 V; V <sub>CE</sub> = 700 V; T <sub>j</sub> = 25 °C	[1]	-	-	0.2	mA
	current (base shorted)	V <sub>BE</sub> = 0 V; V <sub>CE</sub> = 700 V; T <sub>j</sub> = 125 °C	[1]	-	-	0.5	mA
I <sub>CBO</sub>	collector-base cut-off current (emitter open)	$V_{CB} = 700 \text{ V}; I_{E} = 0 \text{ A}$	[1]	-	-	0.2	mA
СЕО	collector-emitter cut-off current (base open)	$V_{CE} = 400 \text{ V}; I_{B} = 0 \text{ A}$	[1]	-	-	0.1	mA
I <sub>EBO</sub>	emitter-base cut-off current (collector open)	$V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}$		-	-	10	mA
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 4 A; I <sub>B</sub> = 0.8 A; <u>Fig. 6</u> ; <u>Fig. 7</u>		-	0.35	1	V
$V_{BEsat}$	base-emitter saturation voltage	I <sub>C</sub> = 4 A; I <sub>B</sub> = 0.8 A; <u>Fig. 8</u>		-	1	1.5	V
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 4 A; T <sub>j</sub> = 25 °C		-	1.07	1.5	V
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 4 A; V <sub>CE</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 9</u> ; <u>Fig. 10</u>		8	12.5	-	
		I <sub>C</sub> = 1 mA; V <sub>CE</sub> = 5 V; T <sub>mb</sub> = 25 °C		10	17	34	
		I <sub>C</sub> = 500 mA; V <sub>CE</sub> = 5 V; T <sub>mb</sub> = 25 °C		13	22	36	
Dynamic ch	aracteristics						
t <sub>on</sub>	turn-on time	I <sub>C</sub> = 5 A; I <sub>Bon</sub> = 1 A; I <sub>Boff</sub> = -1 A;		-	0.65	1	μs
t <sub>s</sub>	storage time	$R_L = 75 \Omega$ ; $T_j = 25 °C$ ; resistive load; Fig. 11; Fig. 12		-	1.8	2.5	μs
		$I_C$ = 5 A; $I_{Bon}$ = 1 A; $V_{BB}$ = -5 V; $L_B$ = 1 $\mu$ H; $T_j$ = 25 °C; inductive load; <u>Fig. 13</u> ; <u>Fig. 14</u>		-	1.2	1.7	μs
		$I_C$ = 5 A; $I_{Bon}$ = 1 A; $V_{BB}$ = -5 V; $L_B$ = 1 $\mu$ H; $T_j$ = 100 °C; inductive load; Fig. 13; Fig. 14		-	1.4	1.9	μs
t <sub>f</sub>	fall time	$I_C$ = 5 A; $I_{Bon}$ = 1 A; $V_{BB}$ = -5 V; $L_B$ = 1 $\mu$ H; $T_{mb}$ = 25 °C; inductive load; Fig. 13; Fig. 14		-	0.02	0.05	μs
		$I_C$ = 5 A; $I_{Bon}$ = 1 A; $V_{BB}$ = -5 V; $L_B$ = 1 $\mu$ H; $T_{mb}$ = 100 °C; inductive load; Fig. 13; Fig. 14		-	0.025	0.1	μs
		$I_C$ = 5 A; $I_{Bon}$ = 1 A; $I_{Boff}$ = -1 A; $R_L$ = 75 $\Omega$ ; resistive load; Fig. 11; Fig. 12		-	0.3	0.5	μs

<sup>[1]</sup> Measured with half-sine wave voltage (curve tracer).

#### NPN power transistor with integrated diode

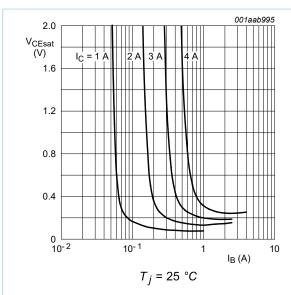


Fig. 6. Collector-emitter saturation voltage as a function of base current; typical values

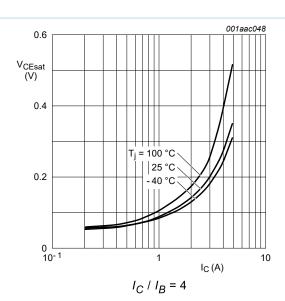


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

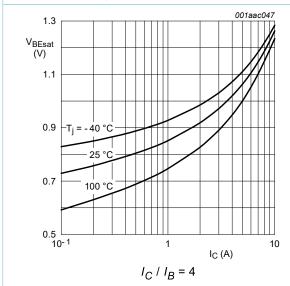


Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

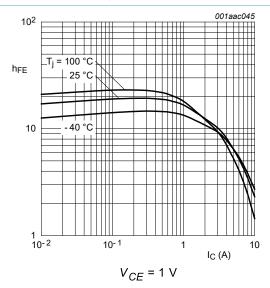


Fig. 9. DC current gain as a function of collector current; typical values

#### NPN power transistor with integrated diode

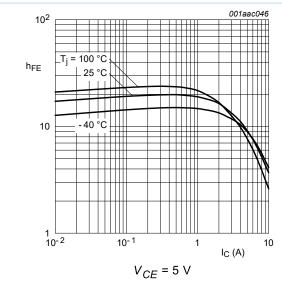


Fig. 10. DC current gain as a function of collector current; typical values

 $V_{IM}$  = -6 to +8 V;  $V_{CC}$  = 250 V;  $t_p$  = 20  $\mu s$ ;  $\delta = \frac{t_p}{T}$  = 0.01  $R_B$  and  $R_L$  calculated from  $I_{Con}$  and  $I_{Bon}$  requirements.

Fig. 11. Test circuit for resistive load switching

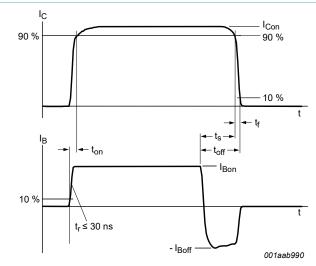
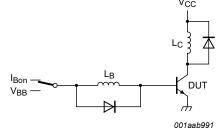


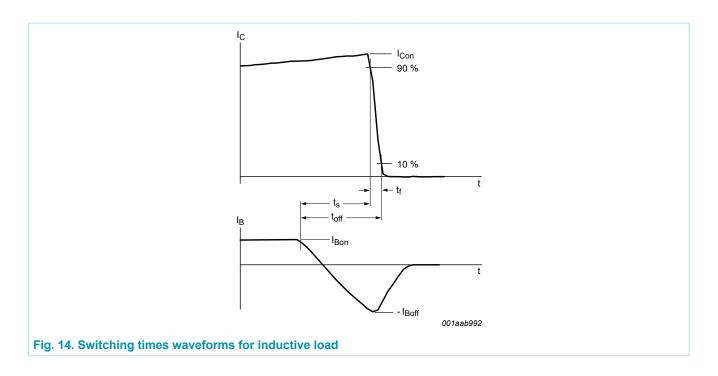
Fig. 12. Switching times waveforms for resistive load



 $V_{CC} = 300 \text{ V}; V_{BB} = -5 \text{ V}; L_C = 200 \mu\text{H}; L_B = 1 \mu\text{H}$ 

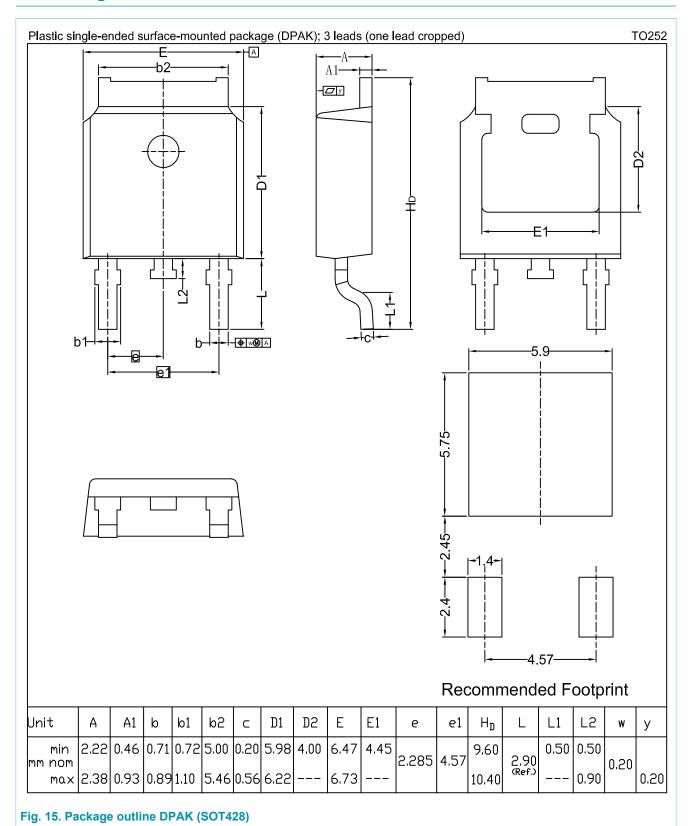
Fig. 13. Test circuit for inductive load switching

### NPN power transistor with integrated diode



NPN power transistor with integrated diode

# 9. Package outline



#### NPN power transistor with integrated diode

# 10. Legal information

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Document status [1][2]	Product status [3]	Definition
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#### NPN power transistor with integrated diode

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